

RF Amplifiers, N-Channel MMBF4416

Features

- This Device is Designed for RF Amplifiers
- Sourced from Process 50
- This is a Pb-Free and Halide Free Device

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Value	Unit
V_{DG}	Drain-Gate Voltage	30	٧
V_{GS}	Gate-Source Voltage	-30	V
I _{GF}	Forward Gate Current	10	mA
T _J , T _{STG}	Junction and Storage Temperature Range	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

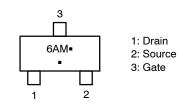
(T_A = 25°C unless otherwise noted.) (Note 1)

Symbol	Parameter	Max	Unit
P _D	Total Device Dissipation Derate above 25°C	225 1.8	mW mW/°C
$R_{ heta JA}$	Thermal Resistance, Junction to Ambient	556	°C/W

^{1.} Device mounted on FR-4 PCB $1.6" \times 1.6" \times 0.06"$.

SOT-23 CASE 318-08

MARKING DIAGRAM



6A = Specific Device Code

M = Date Code

= Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBF4416	SOT-23 (Pb-Free/ Halide Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
OFF CHAR	ACTERISTICS	•			-	-
V _{(BR)GSS}	Gate-Source Breakdown Voltage	$V_{DS} = 0$, $I_{G} = 1 \mu A$	-30	_	-	V
I _{GSS}	Gate Reverse Current	$V_{GS} = -20 \text{ V}, V_{DS} = 0$ $V_{GS} = -20 \text{ V}, V_{DS} = 0, T_A = 150^{\circ}\text{C}$	-	- -	-1 -200	nA nA
V _{GS} (off)	Gate Source Cut-off Voltage	V _{DS} = 15 V, I _D = 1 nA	-2.5	_	-6	V
V_{GS}	Gate Source Voltage	$V_{DS} = 15 \text{ V}, I_D = 0.5 \text{ mA}$	-1	_	-5.5	V
ON CHARA	ACTERISTICS					
I _{DSS}	Zero-Gate Voltage Drain Current	V _{GS} = 15 V, V _{GS} = 0	5	_	15	mA
V _{GS} (f)	Gate-Source Forward Voltage	V _{DS} = 0, I _G = 1 mA	-	-	1	V
SMALL SIG	GNAL CHARACTERISTICS					
IY _{fs} I	Forward Transfer Admittance	V _{DS} = 15 V, V _{GS} = 0, f = 1 kHz	4500	_	7500	μmhos
ly _{os} l	Output Admittance	V _{DS} = 15 V, V _{GS} = 0, f = 1 kHz	-	_	50	μmhos
C _{iss}	Input Capacitance	V _{DS} = 15 V, V _{GS} = 0, f = 1 MHz	-	-	4	pF
C _{rss}	Reverse Transfer Capacitance	V _{DS} = 15 V, V _{GS} = 0, f = 1 MHz	-	-	0.9	pF
C _{oss}	Output Capacitance	V _{DS} = 15 V, V _{GS} = 0, f = 1 MHz	-	-	2	pF
	AL CHARACTERISTICS					
NF	Noise Figure	V_{DS} = 15 V, I_D = 5 mA, R_g = 100 Ω , f = 100 MHz	-	_	2	dB
G _{ps}	Common Source Power Gain	$V_{DS} = 15 \text{ V}, I_D = 5 \text{ mA}, R_a = 100 \Omega, f = 100 \text{ MHz}$	18	_	-	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

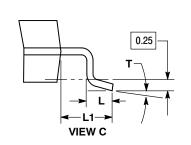


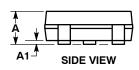
SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

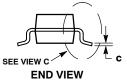
DATE 30 JAN 2018

SCALE 4:1 D – 3X h

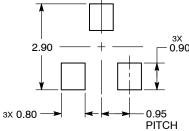
TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

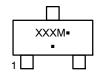
3. ANODE

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE_ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE

2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANO	DDE 3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE

 SOURCE DRAIN 	2. OUTPUT3. INPUT	 ANODE CATHODE 	2. DRAIN 3. SOURCE	2. CATHODE 3. GATE	2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE	STYLE 28: PIN 1. ANODE				
2. CATHODE	2. ANODE				

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DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 1

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3. CATHODE

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